

SEMICONDUCTOR TECHNICAL DATA

KTA1046

EPITAXIAL PLANAR PNP TRANSISTOR

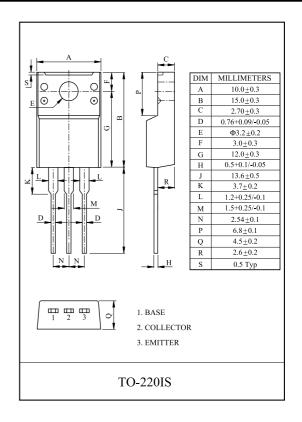
INDUSTRIAL USE.
GENERAL PURPOSE APPLICATION.

FEATURES

- · Low Collector Saturation Voltage
 - : $V_{CE(sat)}$ =-1.0V(Max.) at I_{C} =-2A, I_{B} =-0.2A.
- \cdot Complementary to KTC2026.

MAXIMUM RATING (Ta=25)

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CHARACTERISTIC		SYMBOL	RATING	UNIT				
Collector-Base Voltage		V_{CBO}	-60	V				
Collector-Emitter Voltage		V _{CEO}	-60	V				
Emitter-Base Voltage		V_{EBO}	-7	V				
Collector Current		I_{C}	-3	A				
Base Current		I_{B}	-0.5	A				
Collector Power	Ta=25	P _C	2	W				
Dissipation	Tc=25	1 C	20					
Junction Temperature		T _j	150					
Storage Temperature Range		T_{stg}	-55 150					



ELECTRICAL CHARACTERISTICS (Ta=25)

CHARAC*	TERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Cu	rrent	I_{CBO}	V_{CB} =-60V, I_{E} =0	-	-	-1	μA
Emitter Cut-off Current		I_{EBO}	V_{EB} =-7V, I_{C} =0	-	-	-1	μA
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	I _C =-50mA, I _B =0	-60	-	-	V
DC Current Gain		h _{FE} (1) (Note)	V_{CE} =-5V, I_{C} =-0.5A	100	-	300	
		h _{FE} (2)	V_{CE} =-5V, I_{C} =-3A	20	-	-	
Collector Emitter Saturation Voltage		V _{CE(sat)}	I_{C} =-2A, I_{B} =-0.2A	-	-0.25	-1.0	V
Base-Emitter Voltage		V_{BE}	V_{CE} =-5V, I_{C} =-0.5A	-	-0.7	-1.0	V
Transition Frequency		f_T	V_{CE} =-5V, I_{C} =-0.5A	-	30	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB} =-10V, I_{E} =0, f =1MHz	-	45	-	pF
Switching Time	Turn-on Time	t _{on}	$\begin{array}{c c} O & & OUTPUT \\ \hline \\ I_{B1} & & & \\ \hline \\ 2Outsec & & \\ \end{array}$	-	0.4	-	
	Storage Time	t _{stg}		-	1.7	-	μS
	Fall Time	t _f	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	-	0.5	-	

Note: h_{FE}(1) Classification Y:100 200, GR:150 300

KTA1046

